



Substitute for Form 1449/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/748,090
				Filing Date	December 29, 2003
				First Named Inventor:	Justin K. Brask et al.
				Art Unit	Unknown 2825
				Examiner Name	Unknown V. Yezhikov
Sheet	2	of	2	Attorney Docket Number	P16015C
<b>NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T <sup>2</sup>
VY		Chih-Wei, Yang et al, "Dramatic Reduction of Gate Leakage Current in 1.61nm HfO2 High-K Dielectric Poly-silicon Gate with A1203 Capping Layers", Electronics Letters, Vol. 38, NO. 20, September 2002, pages 1223-1225, XP002288765			
VY		Osten, H.J. et al., "Epitaxial, High-K Dielectrics on Silicon: The Example of Praseodymium Oxide", Microelectronics and Reliability, Elsevier Science Ltd, GB, Vol. 41, 2001, pages 991-994 XP002265638			
VY		PCT International Search Report PCT/US 03/40688			

Examiner Signature	V. Yezhikov	Date Considered	01/04/05
--------------------	-------------	-----------------	----------

\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Substitut f r F rm 1449/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	Not yet assigned
				Filing Date	Herewith
				First Named Inventor:	Justin K. Brask et al.
				Art Unit	Not yet assigned <del>142</del> 2825
				Examiner Name	Not yet assigned V. Yeaslick
				Attorney Docket Number	P16015C

  

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)				
VY ↑		US-	2002/0197790 A1	12/26/2002	Kizilyalli et al.	_____
		US-	6,514,828 B2	2/4/2003	Ahn et al.	_____
		US-	6,436,777 B1	8/20/2002	Ota	_____
		US-	2003/0045080 A1	3/6/2003	Visokay et al.	_____
		US-	6,544,906 B2	4/8/2003	Rotondaro et al.	_____
		US-	6,184,072 B1	2/6/2001	Kaushik et al.	_____
		US-	6,420,279 B1	7/16/2002	Ono et al.	_____
		US-	2003/0032303 A1	2/13/2003	Yu et al.	_____
		US-	5,783,478	7/21/1998	Chau et al.	_____
		US-	6,625,217	4/29/1997	Chau et al.	_____
VY ↓		US-	6,306,742 B1	10/23/2001	Doyle et al.	_____
		US-	5,891,798	4/6/1999	Doyle et al.	_____
		US-				
		US-				

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				

Examiner Signature	V. Yeaslick	Date Considered	01/09/05
--------------------	-------------	-----------------	----------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS.  
**SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

<b>Substitut for F rm 1449/PTO</b>  <b>INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	Not yet assigned
				Filing Date	Herewith
				First Named Inventor:	Justin K. Brask et al.
				Art Unit	Unknown
				Examiner Name	Unknown
Sheet	2	of	2	Attorney Docket Number	P16015C
<b>NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T <sup>2</sup>
VY		Doug Barlage et la. "High Frequency Responset of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages			
VY		ROBERT S. CHAU ET AL. "A 50NM Depleted-Substrate CMOS Transistor (DST)", 2001 IEEE, 4 pages			
VY		"A Method of Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/082,530, filed 2/22/02			
VY		"A Method of Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/285,915, Filed 10/31/02			
VY		"A Method of Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/288,043, Filed 11/5/02			
VY		"A Method of Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/315,268, Filed 12/10/02			
VY		"A Method of Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/338,174, Filed 1/7/03			
VY		"A Method of Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. Unknown, Filed 3/11/03			

Examiner Signature	V. Yerusha	Date Considered	01/04/05
--------------------	------------	-----------------	----------

\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-788-9199) and select option 2.